

	SINGLE CRYSTALLINE SILICON TFT	MONODOMAIN TFT
GRAIN BOUNDARY	NO	NO
CONCENTRATION OF HYDROGEN (cm^{-3})	detection limit	$1 \times 10^{15} - 1 \times 10^{20}$
ESR (cm^{-3})	detection limit	$1 \times 10^{15} - 1 \times 10^{17}$
CRYSTALLINITY	YES	YES
MOBILITY (cm^2/Vs) ($\text{cm}^2/\text{V}\cdot\text{s}$)	P-channel: 300-500 N-channel: 800-1200	P-channel: 200-400 N-channel: 500-1000
S VALUE	0.01 - 0.1	0.03 - 0.3
FORM	formed into single crystalline silicon wafer	semiconductor thin film formed on insulating substrate such as glass (strain point of 550- 750 °C) is used.
PROCESS TEMPERATURE (°C)	800-1100, typically 900-1000	450-700 typically 500-650

FIG. 5